



8TQ...SPbF

SCHOTTKY RECTIFIER

8 Amp

$I_{F(AV)} = 8 \text{ Amp}$
 $V_R = 80 - 100V$

Major Ratings and Characteristics


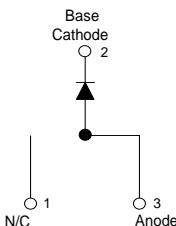
Characteristics	Values	Units
$I_{F(AV)}$ Rectangular waveform	8	A
V_{RRM} range	80 - 100	V
I_{FSM} @tp = 5 μ s sine	850	A
V_F @8 Apk, $T_J = 125^\circ\text{C}$	0.58	V
T_J range	-55 to 175	$^\circ\text{C}$

Description/ Features

The 8TQ .. Schottky rectifier series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175° C junction temperature. Typical applications are in switching power supplies, converters, free-wheeling diodes, and reverse battery protection.

- 175° C T_J operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Lead-Free ("PbF" suffix)

Case Styles

D²PAK

Voltage Ratings

Part number	8TQ080SPbF	8TQ100SPbF
V_R Max. DC Reverse Voltage (V)	80	100
V_{RWM} Max. Working Peak Reverse Voltage (V)		

Absolute Maximum Ratings

Parameters	8TQ	Units	Conditions
$I_{F(AV)}$ Max. Average Forward Current * See Fig. 5	8	A	50% duty cycle @ $T_C = 157^\circ\text{C}$, rectangular wave form
I_{FSM} Max. Peak One Cycle Non-Repetitive Surge Current * See Fig. 7	850	A	5 μs Sine or 3 μs Rect. pulse
	230		10ms Sine or 6ms Rect. pulse
E_{AS} Non-Repetitive Avalanche Energy	7.50	mJ	$T_J = 25^\circ\text{C}$, $I_{AS} = 0.50$ Amps, $L = 60$ mH
I_{AR} Repetitive Avalanche Current	0.50	A	Current decaying linearly to zero in 1 μsec Frequency limited by T_J max. $V_A = 1.5 \times V_R$ typical

Electrical Specifications

Parameters	8TQ	Units	Conditions
V_{FM} Max. Forward Voltage Drop (1) * See Fig. 1	0.72	V	@ 8A
	0.88	V	@ 16A
	0.58	V	@ 8A
	0.69	V	@ 16A
I_{RM} Max. Reverse Leakage Current (1) * See Fig. 2	0.55	mA	$T_J = 25^\circ\text{C}$
	7	mA	$T_J = 125^\circ\text{C}$
C_T Max. Junction Capacitance	500	pF	$V_R = 5V_{DC}$ (test signal range 100Khz to 1Mhz) 25°C
L_S Typical Series Inductance	8	nH	Measured lead to lead 5mm from package body
dv/dt Max. Voltage Rate of Change (Rated V_R)	10000	V/ μs	

(1) Pulse Width < 300 μs , Duty Cycle < 2%

Thermal-Mechanical Specifications

Parameters	8TQ	Units	Conditions
T_J Max. Junction Temperature Range	-55 to 175	$^\circ\text{C}$	
T_{stg} Max. Storage Temperature Range	-55 to 175	$^\circ\text{C}$	
R_{thJC} Max. Thermal Resistance Junction to Case	2.0	$^\circ\text{C}/\text{W}$	DC operation * See Fig. 4
R_{thCS} Typical Thermal Resistance, Case to Heatsink	0.50	$^\circ\text{C}/\text{W}$	Mounting surface, smooth and greased
wt Approximate Weight	2 (0.07)	g (oz.)	
T Mounting Torque	Min.	6 (5)	Kg-cm
	Max.	12 (10)	(lbf-in)
Marking Device	8TQ...S		Case style D ² Pak

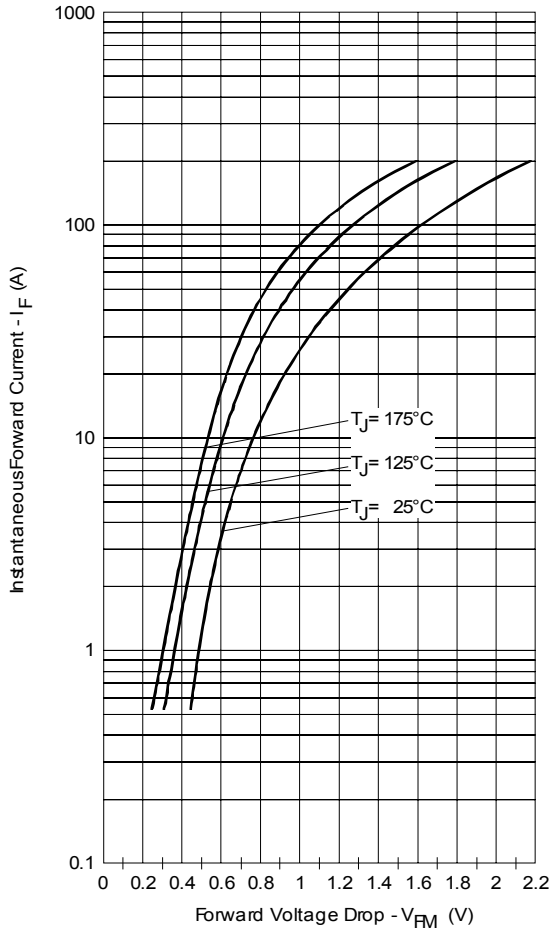


Fig. 1 - Maximum Forward Voltage Drop Characteristics

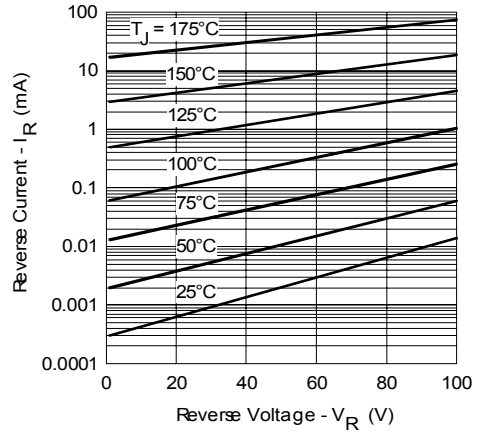


Fig. 2 - Typical Values of Reverse Current Vs. Reverse Voltage

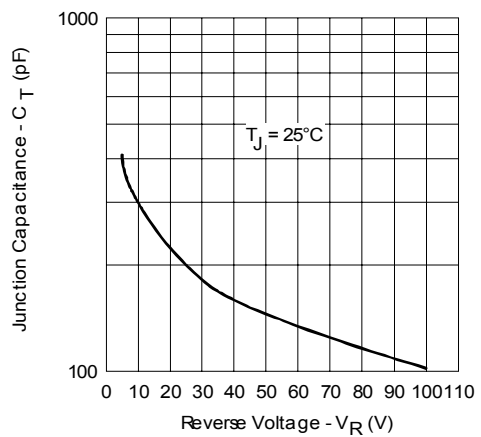


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage

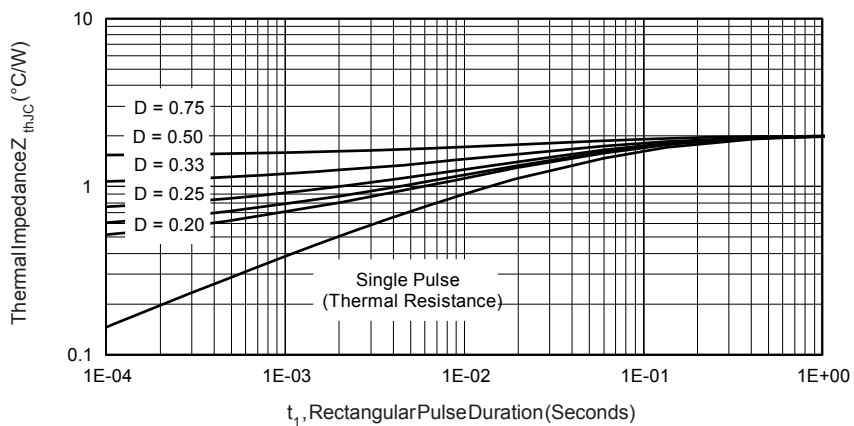


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

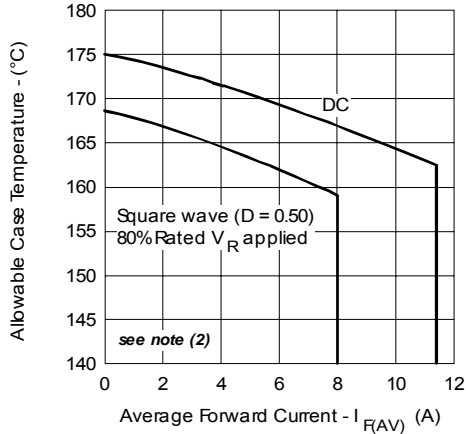


Fig. 5 - Maximum Allowable Case Temperature Vs. Average Forward Current

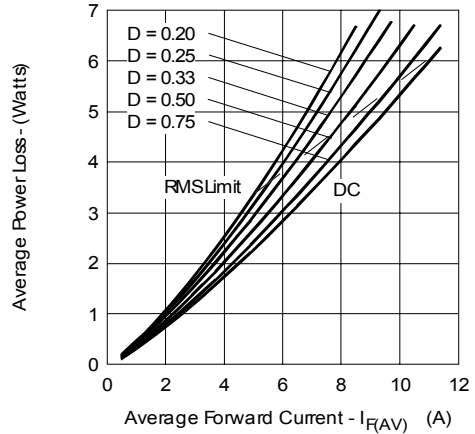


Fig. 6 - Forward Power Loss Characteristics

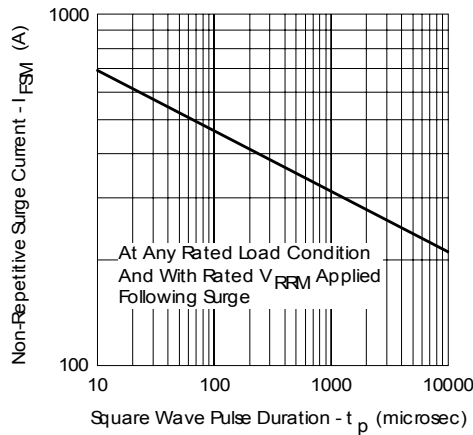


Fig. 7 - Maximum Non-Repetitive Surge Current

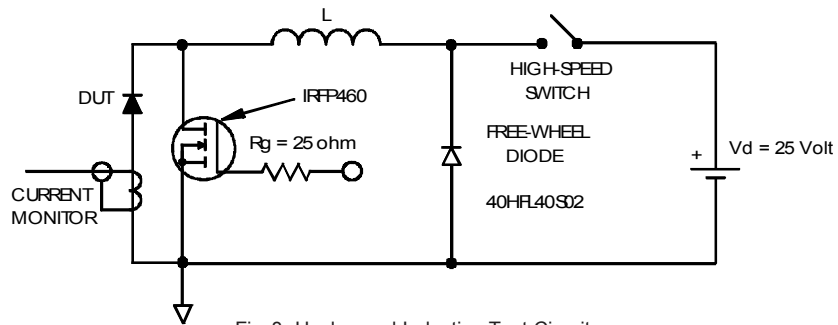


Fig. 8 - Unclamped Inductive Test Circuit

(2) Formula used: $T_c = T_j - (Pd + Pd_{REV}) \times R_{thJC}$;

$Pd = \text{Forward Power Loss} = I_{F(AV)} \times V_{FM} @ (I_{F(AV)} / D)$ (see Fig. 6);

$Pd_{REV} = \text{Inverse Power Loss} = V_{R1} \times I_{R1} (1 - D)$; $I_{R1} @ V_{R1} = 80\% \text{ rated } V_R$

Outline Table

NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
 3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
 5. CONTROLLING DIMENSION: INCH.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.78	.045	.070	
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	4
c2	1.14	1.65	.045	.065	
D	8.51	9.65	.335	.380	3
D1	6.86		.270		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1		1.65		.065	
L2	1.27	1.78	.050	.070	
L3	0.25 BSC		.010 BSC		
L4	4.78	5.28	.188	.208	
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
R	0.51	0.71	.020	.028	
θ	90°	93°	90°	93°	

LEAD ASSIGNMENTS
 HEXFET
 1.- GATE
 2, 4.- DRAIN
 3.- SOURCE

IGBTs, CoPACK
 1.- GATE
 2, 4.- COLLECTOR
 3.- EMITTER

DIODES
 1.- ANODE *
 2, 4.- CATHODE
 3.- ANODE

* PART DEPENDENT.

Conform to JEDEC outline D²Pak (SMD-220)
 Dimensions in millimeters and (inches)

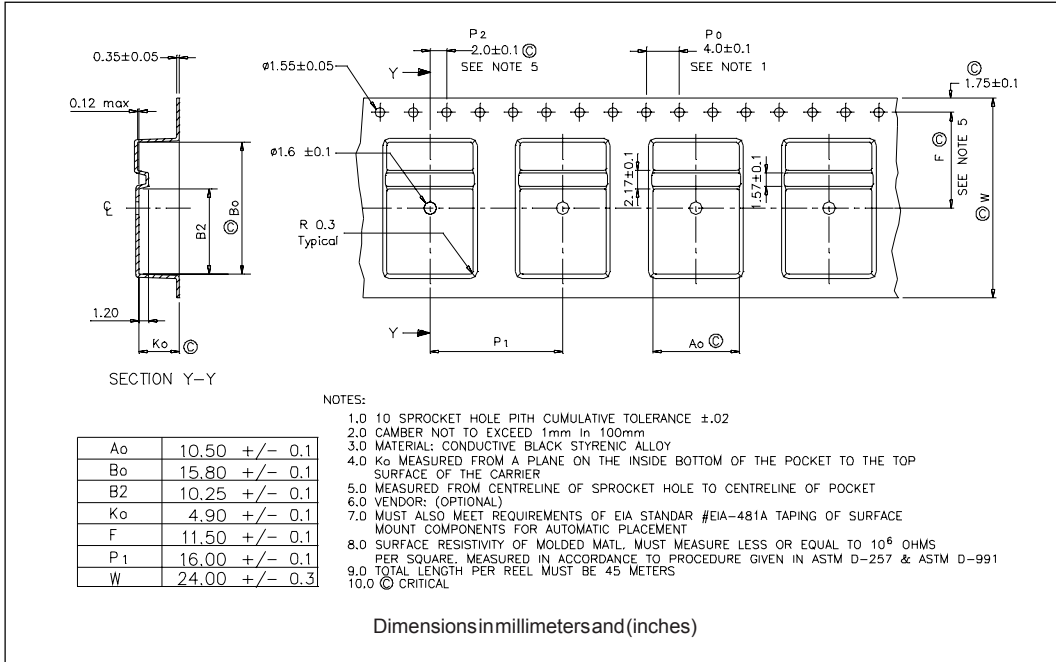
Part Marking Information

EXAMPLE: THIS IS A 8TQ100S
 LOT CODE 8024
 ASSEMBLED ON WW 02, 2000

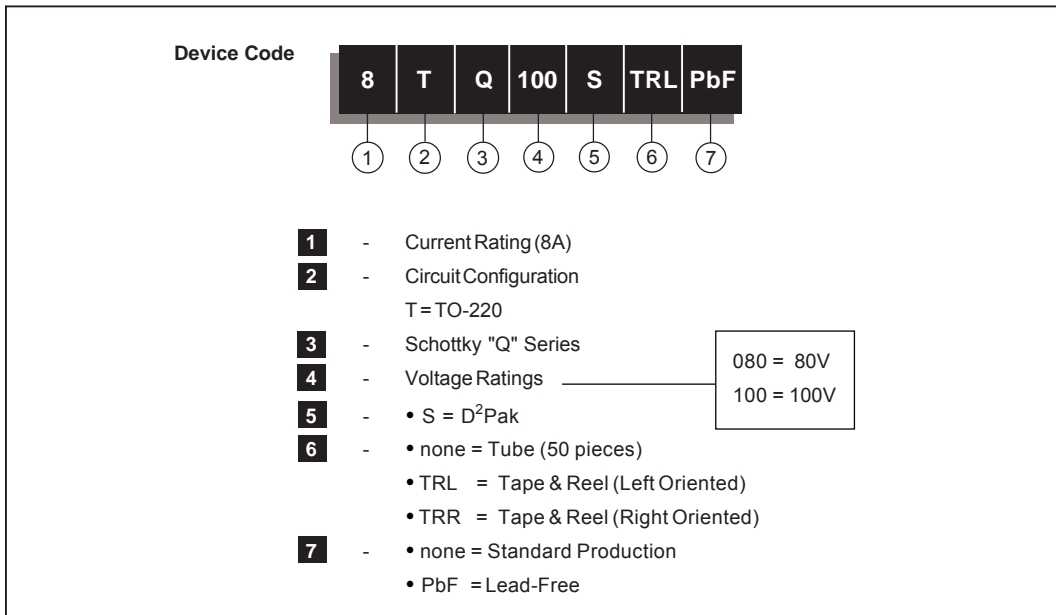
Note: "P" in assembly line position indicates "Lead-Free"

INTERNATIONAL RECTIFIER LOGO
 PART NUMBER
 DATE CODE
 YEAR 0 = 2000
 WEEK 02
 P = LEAD-FREE

Tape & Reel Information



Ordering Information Table



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8TQ100
*****
*   This model has been developed by   *
*   Wizard SPICE MODEL GENERATOR (1999) *
*   (International Rectifier Corporation) *
*   Contain Proprietary Information   *
*****
*   SPICE Model Diode is composed by a   *
*   simple diode plus paralalled VCG2T   *
*****
.SUBCKT 8TQ100 ANO CAT
D1 ANO 1 DMOD (0.07089)
*Define diode model
.MODEL DMOD D(IS=1.15938021883115E-03A,N=1.95244918720315,BV=120V,
+ IBV=5.37891460505463A,RS= 0.00127602,CJO=9.9895753025115E-09,
+ VJ=2.30070034831946,XTI=2, EG=0.758916909331649)
*****
*Implementation of VCG2T
VX 1 2 DC 0V
R1 2 CAT TRES 1E-6
.MODEL TRES RES(R=1,TC1=-90.2420977904848)
GP1 ANO CAT VALUE={-ABS(I(VX))*(EXP(((1.635248E-02/-90.2421)*(V(2,CAT)*1E6)/(I(VX)+1E-6)-
1))+1)*4.011038E-03*ABS(V(ANO,CAT)))-1}
*****
.ENDS 8TQ100

Thermal Model Subcircuit
.SUBCKT 8TQ100 5 1

CTHERM1 5 4 1.45E+00
CTHERM2 4 3 4.54E+00
CTHERM3 3 2 1.09E+01
CTHERM4 2 1 1.01E+02

RTHERM1 5 4 2.49E+00
RTHERM2 4 3 5.20E-04
RTHERM1 3 2 5.43E-01
RTHERM1 2 1 3.05E-02

.ENDS 8TQ100
    
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Data and specifications subject to change without notice.
 This product has been designed and qualified for Industrial Level and Lead-Free.
 Qualification Standards can be found on IR's Web site.



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